

Features

- Advanced Shield Gate Trench technology
- Super Low Gate Charge
- High-Speed Switching
- 100% EAS Guaranteed
- Green Device Available

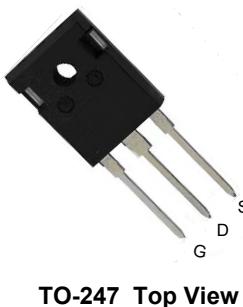
Product Summary



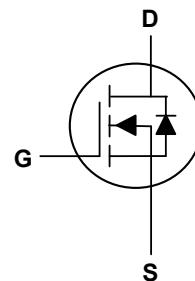
V_{DS}	150	V
I_D	200	A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	4.0	mΩ

Applications

- High Frequency Point-of-Load,Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch



TO-247 Top View



Absolute Maximum Ratings($T_c=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ¹	I_D	200	A
Continuous Drain Current ¹ $T_c=100^\circ\text{C}$	I_D	122	A
Pulsed Drain Current ²	I_{DM}	768	A
Single Pulse Avalanche Energy ³	E_{AS}	720	mJ
Total Power Dissipation ⁴	P_D	820	W
Storage Temperature Range	T_{STG}	-55 to 150	°C
Operating Junction Temperature Range	T_J	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Unit
Thermal Resistance Junction-Ambient ¹	$R_{\theta JA}$	---	62.5	°C/W
Thermal Resistance Junction-Case ¹	$R_{\theta JC}$	---	0.3	°C/W

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}}=0\text{V}$, $I_D=250\mu\text{A}$	150	---	---	V
Static Drain-Source On-Resistance	$R_{\text{DS}(\text{ON})}$	$V_{\text{GS}}=10\text{V}$, $I_D=20\text{A}$	---	3.4	4.0	$\text{m}\Omega$
Gate Threshold Voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{GS}}=V_{\text{DS}}$, $I_D = 250\mu\text{A}$	2	---	4	V
Drain-Source Leakage Current	I_{DSS}	$V_{\text{DS}}=150\text{V}$, $V_{\text{GS}}=0\text{V}$	---	---	1	μA
Gate-Source Leakage Current	I_{GSS}	$V_{\text{GS}}=\pm 20\text{V}$, $V_{\text{DS}}=0\text{V}$	---	---	± 100	nA
Total Gate Charge	Q_g	$V_{\text{DS}}=75\text{V}$, $V_{\text{GS}}=10\text{V}$, $I_D=20\text{A}$	---	136	---	nC
Gate-Source Charge	Q_{gs}		---	18	---	
Gate-Drain Charge	Q_{gd}		---	12	---	
Turn-On Delay Time	$T_{\text{d(on)}}$	$V_{\text{DD}}=75\text{V}$, $V_{\text{GS}}=10\text{V}$, $R_G=10\Omega$, $I_D=20\text{A}$	---	30	---	ns
Rise Time	T_r		---	25	---	
Turn-Off Delay Time	$T_{\text{d(off)}}$		---	80	---	
Fall Time	T_f		---	46	---	
Input Capacitance	C_{iss}	$V_{\text{DS}}=75\text{V}$, $V_{\text{GS}}=0\text{V}$, $f=1\text{MHz}$	---	9200	---	pF
Output Capacitance	C_{oss}		---	870	---	
Reverse Transfer Capacitance	C_{rss}		---	25	---	

Drain-Source Diode Characteristics

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Continuous Source Current ¹	I_s		---	---	200	A
Diode Forward Voltage ²	V_{SD}	$V_{\text{GS}}=0\text{V}$, $I_s=20\text{A}$, $T_J=25^\circ\text{C}$	---	---	1.5	V

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{\text{DD}}=50\text{V}$, $R_G=25\Omega$, $L=0.4\text{mH}$
- 4.The power dissipation is limited by 150°C junction temperature

Typical Characteristics

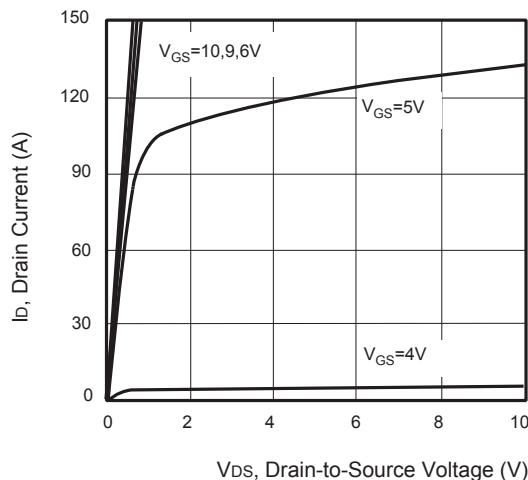


Figure 1. Output Characteristics

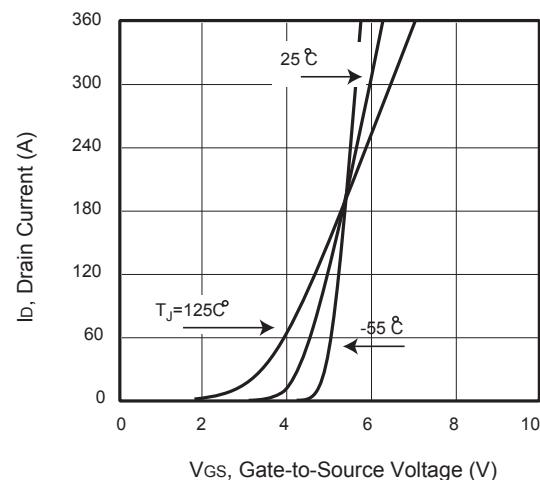


Figure 2. Transfer Characteristics

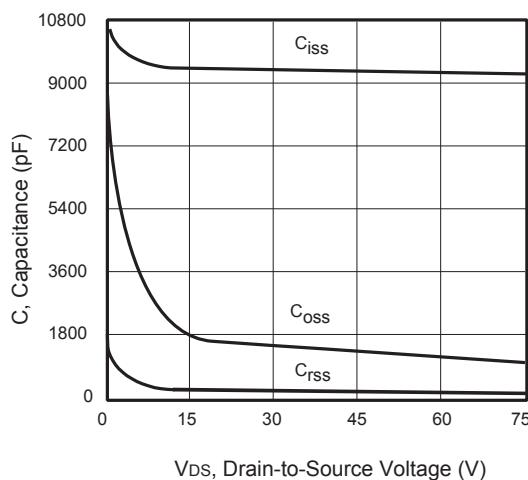


Figure 3. Capacitance

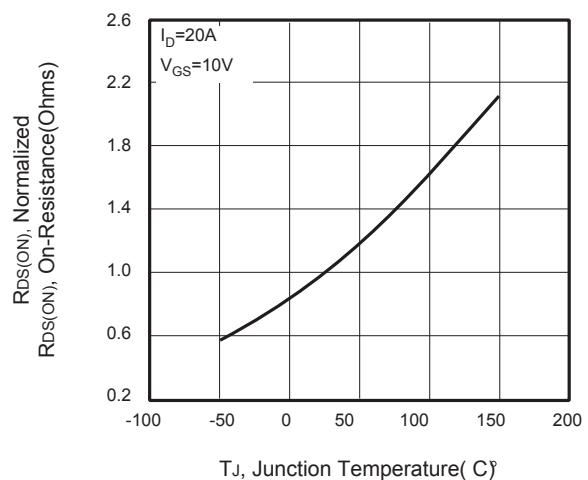


Figure 4. On-Resistance Variation with Temperature

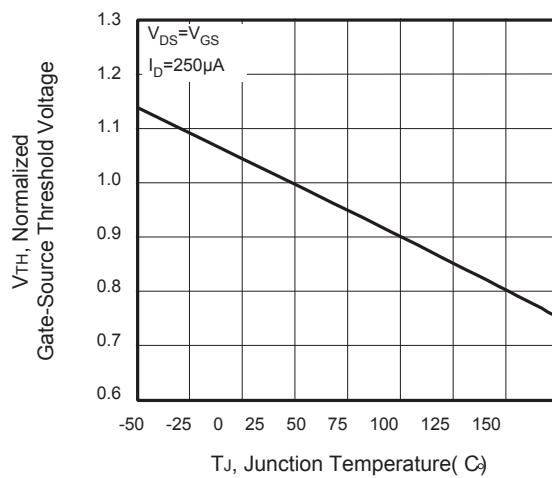


Figure 5. Gate Threshold Variation with Temperature

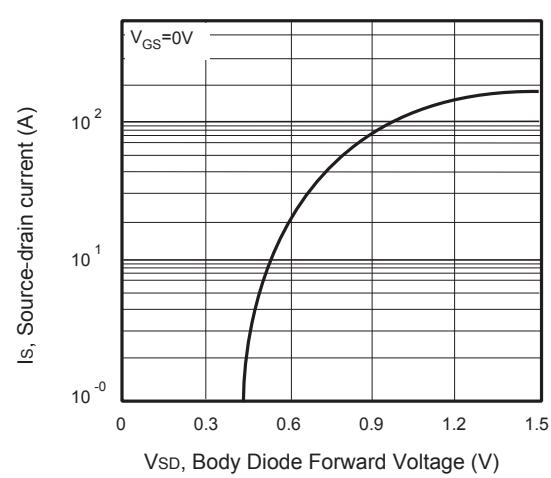
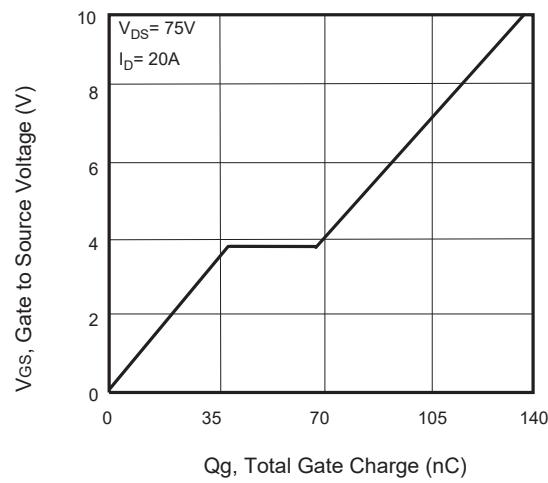
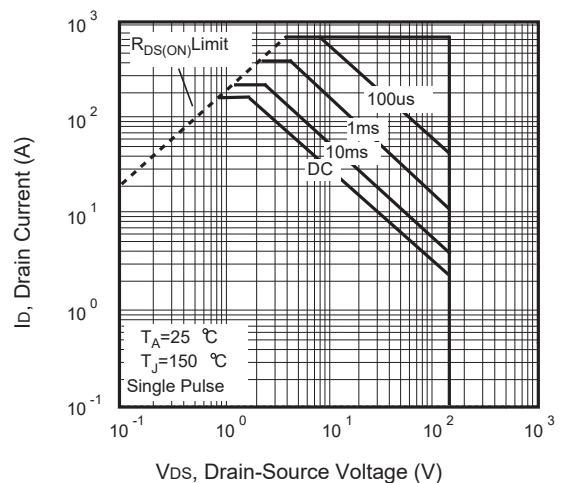
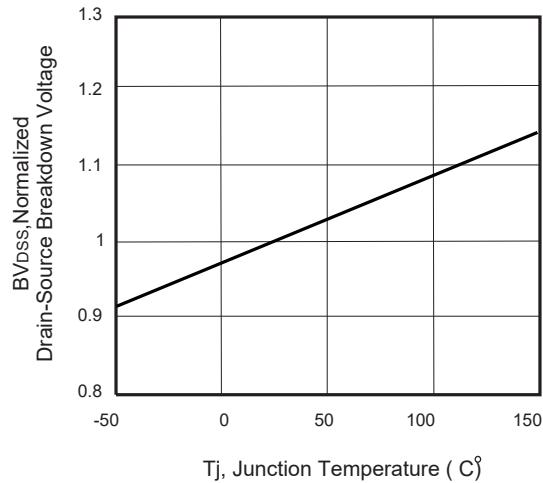
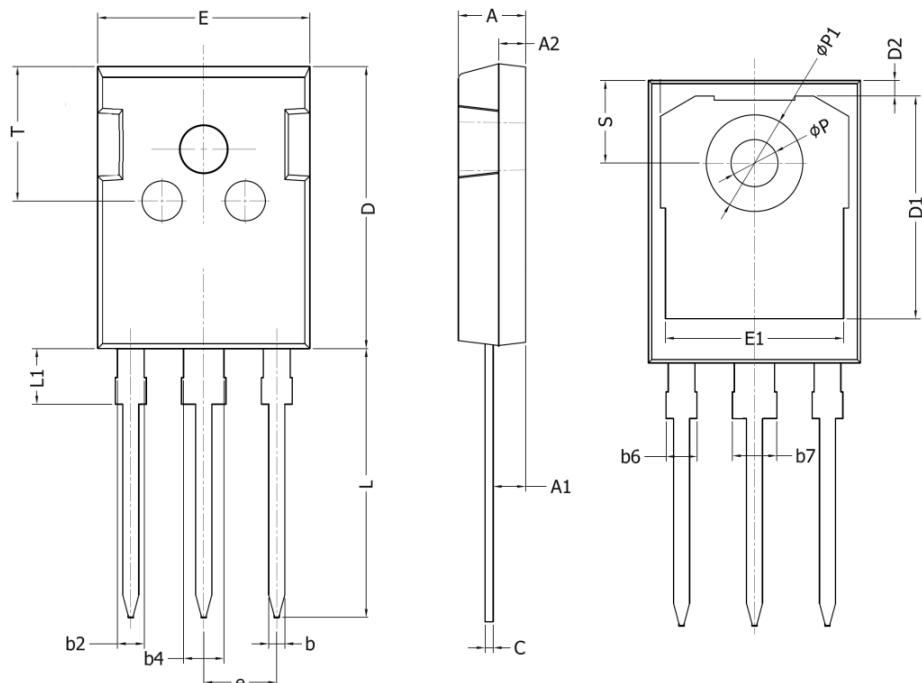


Figure 6. Body Diode Forward Voltage Variation with Source Current


Figure 7. Gate Charge

Figure 8. Maximum Safe Operating Area

Figure 9. Breakdown Voltage Variation VS Temperature

TO-247 Package Outline Dimensions



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	4.90	5.20
A1	2.31	2.51
A2	1.9	2.1
b	1.16	1.26
b2	1.96	2.06
b4	2.96	3.06
b6	-	2.25
b7	-	3.25
C	0.59	0.66
D	20.90	21.20
D1	16.25	16.85
D2	1.05	1.35
E	15.75	16.10
E1	13.00	13.60
e	5.436 BSC	
L	19.80	20.20
L1	-	4.30
P	3.40	3.60
P1	7.00	7.40
S	6.05	6.25
T	9.80	10.20